





CEM4948

-60V ▲ 90mΩ ▲ -3.1A ▲ Dual Si MOSFET





Super high dense cell density for extremely low R_{DS(ON)} High power and current handling capability





MAXIMUM RATINGS

Parameter (T _A = 25°C, unless otherwise noted)	Characteristics	
Drain-Source Voltage	V _{DS}	-60V
Gate-Source Voltage	V _{GS}	±20V
Continuous Drain Current	I _D	-3.1A
Pulsed Drain Current Note 1	I _{DM}	-20A
Maximum Power Dissipation	P _D	2W
Operating and Storage Temperature Range	T _J , T _{STG}	-55°C to +150°C

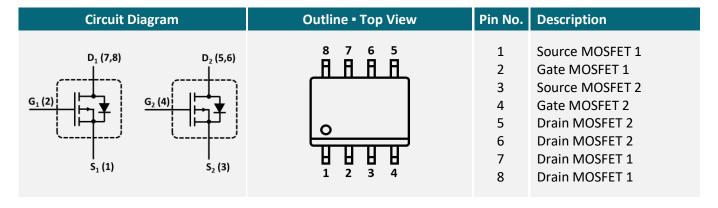
THERMAL CHARACTERISTICS

Parameter	Symbol	Limit
Thermal Resistance, Junction-to-Ambient Note 2	R _{TH_JA}	62.5°C/W

APPLICATIONS

DC/DC	DC	Load	Power	USB
Converter	Fan	Switches	Banks	Storage
			4	Ŷ

PIN DESCRIPTION





ELECTRICAL CHARACTERISTICS ▲ T_A = 25°C, unless otherwise noted

Item	Condition	Symbol	Min.	Тур.	Max.	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	$V_{GS} = 0V$, $I_D = -250\mu A$	BV_{DSS}	-60			V
Zero Gate Voltage Drain Current	$V_{DS} = -60V, V_{GS} = 0V$	I _{DSS}			-2	μΑ
Gate Body Leakage Current, Forward	$V_{GS} = 20V$, $V_{DS} = 0V$	I _{GSSF}			100	nA
Gate Body Leakage Current, Reverse	$V_{GS} = -20V, V_{DS} = 0V$	I _{GSSR}			-100	nA
On Characteristics Note 3						
Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = -250 \mu A$	$V_{GS(th)}$	-1		-3	V
Static Drain-Source On-Resistance	$V_{GS} = -10V$, $I_D = -3.1A$	R _{DS(ON)}		90	120	mΩ
Static Drain-Source On-Resistance	$V_{GS} = -4.5V$, $I_D = -2.8A$	R _{DS(ON)}		120	150	mΩ
Forward Transconductance	$V_{DS} = -15V$, $I_D = -3.1A$	g _{FS}		7		S
Dynamic Characteristics Note 4						
Input Capacitance	$V_{DS} = -30V$, $V_{GS} = 0V$, $f = 1MHz$	C _{ISS}		780		pF
Output Capacitance	$V_{DS} = -30V$, $V_{GS} = 0V$, $f = 1MHz$	Coss		170		pF
Reverse Transfer Capacitance	V_{DS} = -30V, V_{GS} = 0V, f = 1MHz	C_{RSS}		49		pF
Switching Characteristics Note 4						
Turn-On Delay Time	V_{DD} = -30V, V_{GS} = -10V, I_D = -1A, $R_{G(ext)}$ = 6Ω	t _{D(ON)}		13	45	ns
Turn-On Rise Time	V_{DD} = -30V, V_{GS} = -10V, I_D = -1A, $R_{G(ext)}$ = 6Ω	t_R		9	30	ns
Turn-Off Delay Time	V_{DD} = -30V, V_{GS} = -10V, I_D = -1A, $R_{G(ext)}$ = 6Ω	t _{D(OFF)}		48	150	ns
Turn-Off Fall Time	V_{DD} = -30V, V_{GS} = -10V, I_D = -1A, $R_{G(ext)}$ = 6Ω	t _F		22	75	ns
Total Gate Charge	$V_{DS} = -30V$, $V_{GS} = -10V$, $I_{D} = -3.1A$	Q_{G}		21	29	nC
Gate Source Charge	$V_{DS} = -30V$, $V_{GS} = -10V$, $I_{D} = -3.1A$	Q_{GS}		3		nC
Gate Drain Charge	$V_{DS} = -30V$, $V_{GS} = -10V$, $I_D = -3.1A$	Q_GD		4		nC
Drain-Source Diode Characteristics a	nd Maximum Ratings					
Drain-Source Diode Forward Current Note 2		Is			-2	Α
Drain-Source Diode Forward Voltage Note 3	V _{GS} = 0V, I _S = -2A	V_{SD}			-1.2	V

Notes

1: Repetitive Rating: Pulse width limited by maximum junction temperature

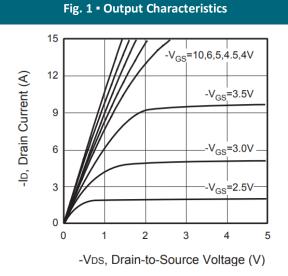
2: Surface Mounted on FR4 Board, t ≤ 10 sec

3: Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.

4: Guaranteed by design, not subject to production testing.

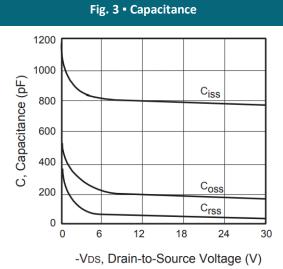


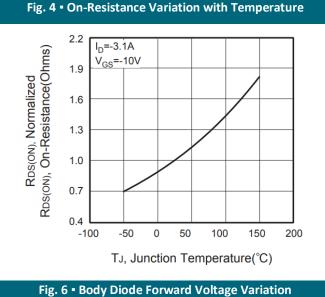
REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

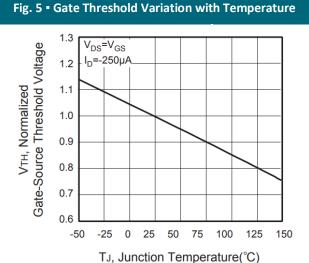


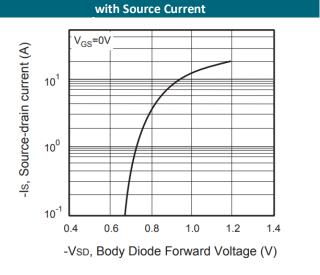
(A) 12 25°C 7 25

Fig. 2 • Transfer Characteristics









MGT ▲ Manufacturer Group of Technology



REFERENCE DATA A TYPICAL DEVICE PERFORMANCE



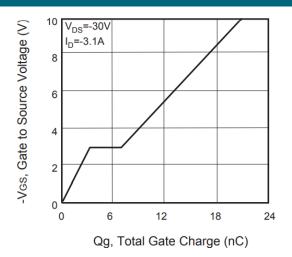


Fig. 8 • Maximum Safe Operating Area

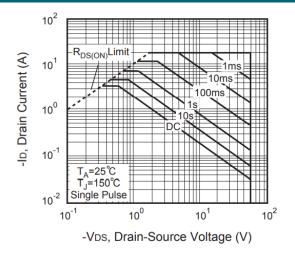


Fig. 9 - Breakdown Voltage Variation vs. Temperature

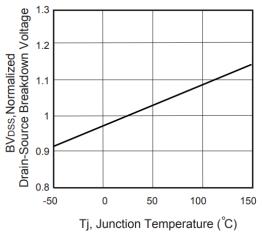


Fig. 10 • Switching Test Circuit

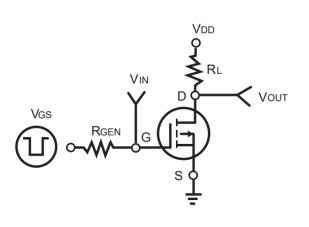
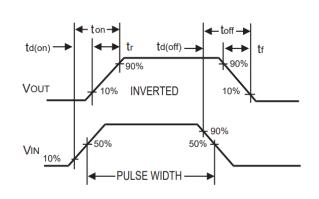


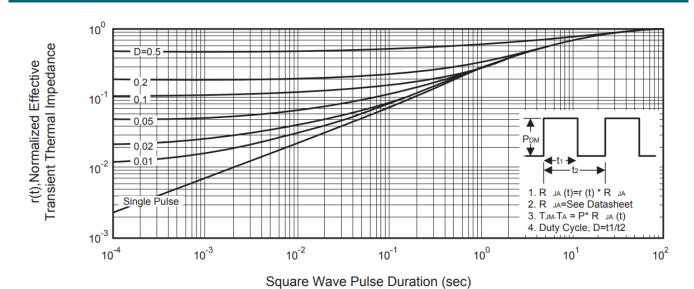
Fig. 11 • Switching Waveforms



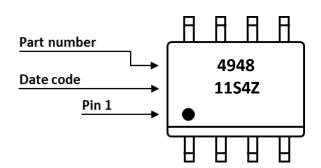


REFERENCE DATA A TYPICAL DEVICE PERFORMANCE

Fig. 12 • Normalized Thermal Transient Impedance Curve

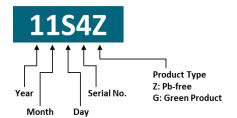


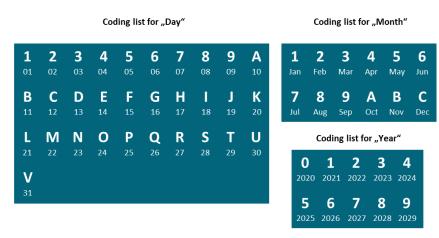
PART MARKING



DATE CODE

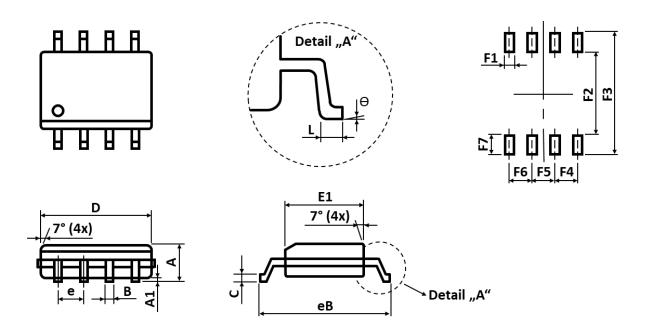
Example: 11S4Z







PACKAGE OUTLINE AND RECOMMENDED PAD LAYOUT



Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
Α	1.350	-	1.750
A1	0.100	-	0.250
В	0.310	-	0.510
С	0.170	-	0.250
D	4.690	-	5.000

Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
3.700		4.060
5.800		6.200
	1.270	
0.400		0.950
0°	-	8°
	(Min.) 3.700 5.800 0.400	(Min.) (Typ.) 3.700 5.800 1.270 0.400

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F1	-	0.500	-
F2	-	4.250	-
F3	-	6.250	-
F4	-	1.270	-

Sym	Millimeters (Min.)	Millimeters (Typ.)	Millimeters (Max.)
F5	-	1.270	-
F6	-	1.270	-
F7	-	1.000	-

Notes: 1. The suggested land pattern dimensions have been provided for reference only.

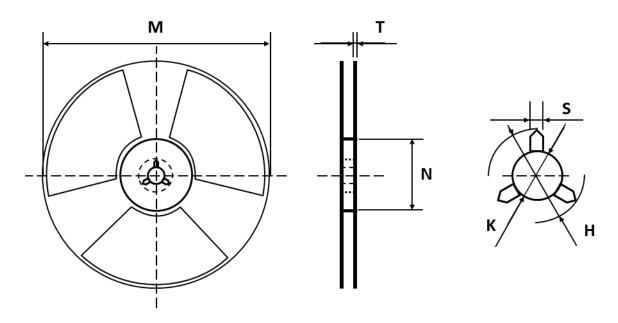
2. For further information, please reference document IPC-7351A.

ORDERING INFORMATION

Part Number	Package	Packing	Reel Qty.	Inner Box Qty.	Outer Box Qty.
CEM4948	SO8	13" Reel	2,500pcs	5,000pcs	40,000pcs

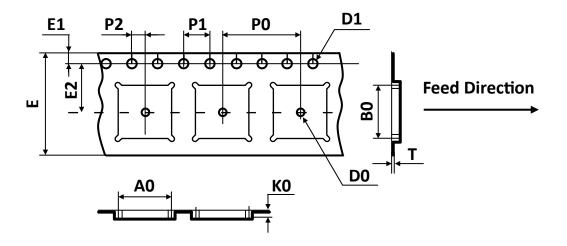


REEL DIMENSIONS ▲ All dimensions in mm



Tape Size	Reel Size	M	N	Т	Н	K	S
12mm	Ø330	Ø330.00	Ø100.00	2.20	20.00	13.20	3.00
12111111	9 550	±2.00	±0.50	±0.20	±1.00	±0.20	±1.00

TAPE DIMENSIONS ▲ All dimensions in mm

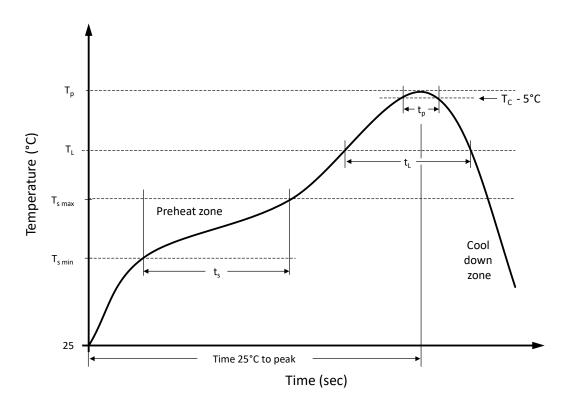


Package	Α0	В0	КО	D0	D1	E	E1	E2	Р0	P1	P2	T
SO8	6.50	5.30	2.05	1.50	1.50	12.00	1.75	5.50	8.00	4.00	2.00	0.25
308	±0.10	±0.10	±0.15	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.10	±0.05	±0.02

Note: All dimensions meet EIA-481-D requirements.



RECOMMENDED REFLOW SOLDERING PROFILE



Recommended reflow soldering conditions ▲ **Refer to JEDEC J-STD-020E**

Profile Features		Sn-Pb Eutetic Assembly	Pb-Free Assembly
Preheat temperature min.	$T_{s min}$	100 °C	150 °C
Preheat temperature max.	T _{s max}	150 °C	200 °C
Preheat time t _s from T _{s min} to T _{s max}	ts	120 seconds	120 seconds
Ramp-up rate (T₁ to Tp)		max. 3 °C/second	max. 3 °C/second
Liquidous temperature	T_L	183 °C	217 °C
Time t _L maintained above T _L	t _L	150 seconds max.	150 seconds max.
Peak package body temperature	Tp	235°C	260°C
Timeframe of within 5°C below and up to max actual peak body temperature	t _p	20 seconds max.	30 seconds max.
Ramp-down rate (T _L to T _p)		max. 6 °C/second	max. 6 °C/second
Time 25°C to peak temperature		max. 6 minutes	max. 8 minutes



REVISION TABLE

Revision	Date	Status	Notes
001	30/09/2022	Initial release	Initial publication

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